

Dual P-channel MOSFET

ELM34801AA-N

General description

ELM34801AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

Features

- $V_{ds} = -30V$
- $I_d = -6A$
- $R_{ds(on)} < 50m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} < 80m\Omega$ ($V_{gs} = -4.5V$)

Maximum absolute ratings

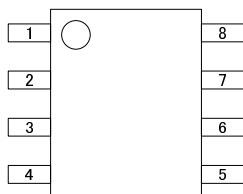
Parameter	Symbol	Limit	Unit	Note
Drain-source voltage	V_{ds}	-30	V	
Gate-source voltage	V_{gs}	± 20	V	
Continuous drain current	I_d	$T_a = 25^\circ C$	-6	A
		$T_a = 70^\circ C$	-5	
Pulsed drain current	I_{dm}	-30	A	3
Power dissipation	P_d	$T_a = 25^\circ C$	2.5	W
		$T_a = 70^\circ C$	1.3	
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$	

Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	Steady-state	$R\theta_{ja}$		62.5	$^\circ C/W$	

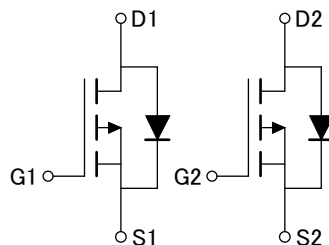
Pin configuration

SOP-8 (TOP VIEW)



Pin No.	Pin name
1	SOURCE1
2	GATE1
3	SOURCE2
4	GATE2
5	DRAIN2
6	DRAIN2
7	DRAIN1
8	DRAIN1

Circuit



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Electrical characteristics

T_a=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	I _d =-250 μA, V _{gs} =0V	-30			V	
Zero gate voltage drain current	I _{dss}	V _{ds} =-24V, V _{gs} =0V			-1	μA	
		V _{ds} =-20V, V _{gs} =0V, T _j =125°C			-10		
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±20V			±100	nA	
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =-250 μA	-0.9	-1.5	-3.0	V	
On state drain current	I _{d(on)}	V _{gs} =-10V, V _{ds} =-5V	-30			A	1
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =-10V, I _d =-6A		40	50	mΩ	1
		V _{gs} =-4.5V, I _d =-5A		65	80	mΩ	
Forward transconductance	G _{fs}	V _{ds} =-10V, I _d =-6A		16		S	1
Diode forward voltage	V _{sd}	I _f =-1A, V _{gs} =0V			-1.2	V	1
Max. body-diode continuous current	I _s				-2.1	A	
Pulsed current	I _{sm}				-4	A	3
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}	V _{gs} =0V, V _{ds} =-15V, f=1MHz		530		pF	
Output capacitance	C _{oss}			135		pF	
Reverse transfer capacitance	C _{rss}			70		pF	
SWITCHING PARAMETERS							
Total gate charge	Q _g	V _{gs} =-10V, V _{ds} =-15V I _d =-6A		10.0	14.0	nC	2
Gate-source charge	Q _{gs}			2.2		nC	2
Gate-drain charge	Q _{gd}			2.0		nC	2
Turn-on delay time	t _{d(on)}	V _{gs} =-10V, V _{ds} =-15V I _d ≈ -1A, R _l =1 Ω, R _{gen} =6 Ω		5.7		ns	2
Turn-on rise time	t _r			10.0		ns	2
Turn-off delay time	t _{d(off)}			18.0		ns	2
Turn-off fall time	t _f			5.0		ns	2
Body diode reverse recovery time	t _{rr}	I _f =-5A, dI/dt=100A/μs		15.5		ns	
Body diode reverse recovery charge	Q _{rr}	I _f =-5A, dI/dt=100A/μs		7.9		nC	

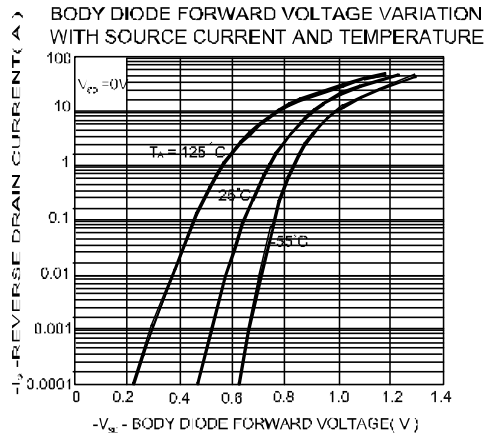
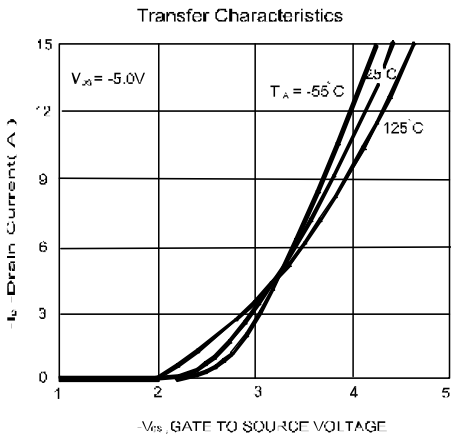
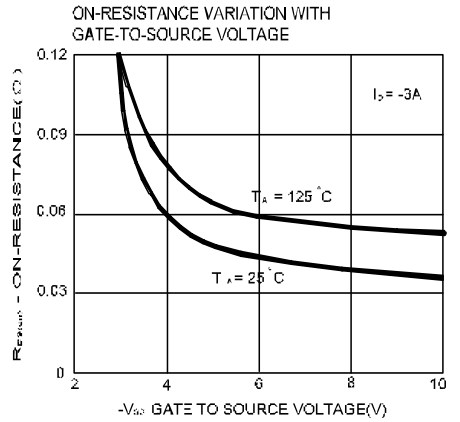
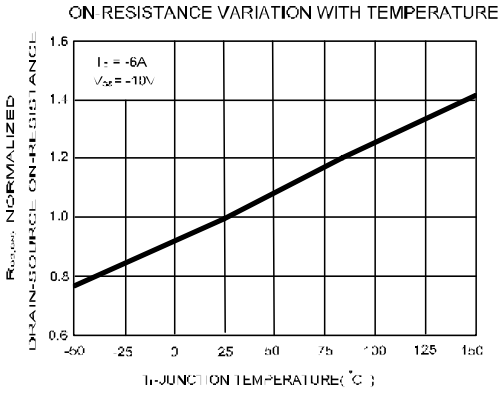
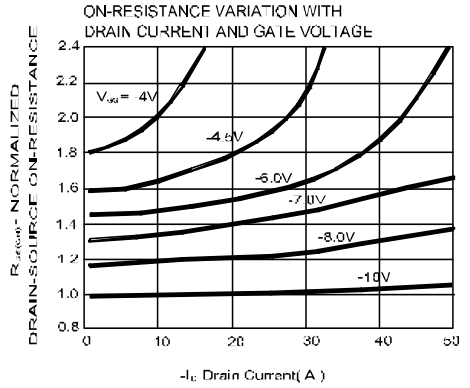
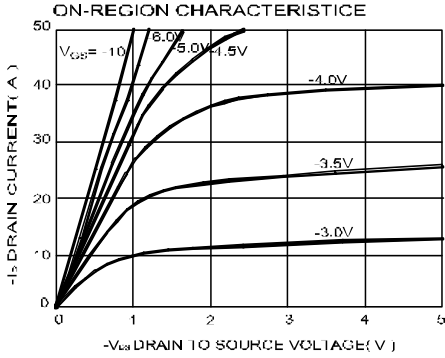
NOTE :

1. Pulsed width ≤ 300 μsec and Duty cycle ≤ 2%.
2. Independent of operating temperature.
3. Pulsed width limited by maximum junction temperature.
4. Duty cycle ≤ 1%.

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Typical electrical and thermal characteristics



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